

060N04T-D3

40V N-Channel Super Trench Power MOSFET



康比電子
HORNBY ELECTRONIC

Description

060N04T-D3 is uses Super Trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications

General Features

- Advanced shielded-gate technology
- Ultra-low on-resistance and gate-charge
- RoHS compliant

MAIN CHARACTERISTICS

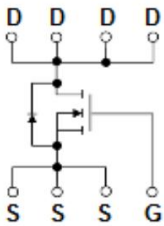
ID	63A
VDSS	40v
R _{DS(ON)Typ} (at VGS=10V)	5.3mΩ

Application

- DC/DC Converter
- Motor controllers
- Battery-driven electronic products, electrical equipment and machines



PDFN3×3-8L



Package Marking and Ordering Information

Device Marking	Device	Device Package	Quantity
060N04T	060N04T-D3	PDFN3×3-8L	5000 pcs/Tape & Reel

Absolute maximum ratings

Symbol	Parameter		Limit	Unit
V _{DSS}	Drain-source voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current -continuous(TC=25℃) (1)		63	A
	Drain Current -continuous(TC=100℃) (1)		40	
I _{DM}	Drain Current-Pulsed (4)		144	A
P _D	Power Dissipation	T _c =25℃	38	W
E _{AS}	Single pulsed avalanche energy (5)(6)		34	mJ
T _J , T _{STG}	Operating and Storage Temperature Range		-50~150	℃

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	3.3	℃/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient (3)	62	℃/W

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Electrical Characteristics $T_c=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Static Characteristics						
BV_{DSS}	Drain Source breakdown voltage	$V_{GS}=0V, I_D=250\mu A, T_J=25^{\circ}\text{C}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
I_{GSS}	Gate-to-Source Forward Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	-	2.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=10A$	-	5.3	6.0	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	7.5	9.8	m Ω
R_G	Gate Resistance	$f = 1 \text{ MHz}$	-	3.8	-	Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 20V$ $f = 1.0MHz$	-	1000	-	pF
C_{oss}	Output Capacitance		-	395	-	pF
Cr_{ss}	Reverse Transfer Capacitance		-	35	-	pF

SWITCHING Characteristics

$T_{D(on)}$	Turn-on Delay Time	$V_{DD} = 20V$ $V_{GS} = 10V$ $R_G = 3\Omega$ $I_D = 20A$	-	8	-	ns
T_r	Turn-on Rise Time		-	6	-	ns
$T_{D(off)}$	Turn-off Delay Time		-	16	-	ns
T_f	Turn-off Fall Time		-	4	-	ns
Q_g	Total Gate Charge	$V_{DD} = 20V$ $V_{GS} = 10V$ $I_D = 15A$	-	18	-	nC
Q_{gs}	Gate Source Charge		-	3.4	-	nC
Q_{gd}	Gate Drain Charge		-	2	-	nC

Drain-Source Diode Characteristics and Maximum Ratings

V_{SD}	Drain-Source Diode Forward Voltage	$I_S = 10A, V_{GS} = 0V$	-	-	1.2	V
T_{rr}	Reverse Recovery Time	$I_S = 20A, V_{GS} = 0V$ $di/dt = 100A/\mu s$	-	36	-	ns
Q_{rr}	Reverse Recovery Charge		-	21	-	nC

Notes:

- Limited by package.
- Rated according to $R_{\theta JC}$
- Rated according to $R_{\theta JA}$
- Surface-mounted on 1 inch² FR4 board, 2 oz Cu
- Limited by maximum T_J
- Starting $T_J = 25^{\circ}\text{C}$, $I_{AS} = 17A$, $L = 0.1mH$, $V_{DD} = 20V$, $V_{GS} = 10V$
- Pulse width limited by maximum T_J

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

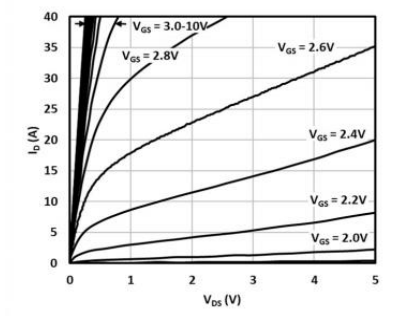


Fig. 1 Output characteristics

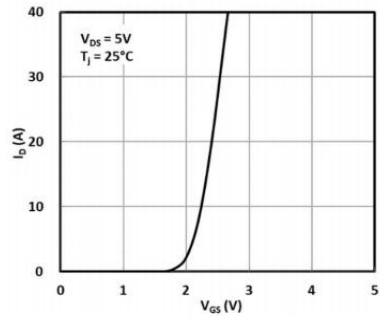


Fig. 2 Transfer characteristics

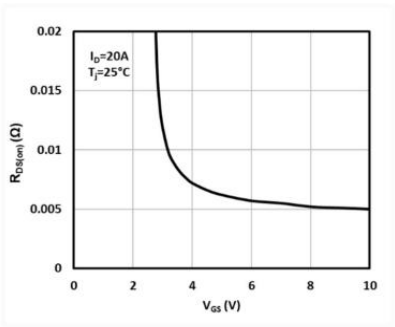


Fig.3 On-resistance vs. gate voltage

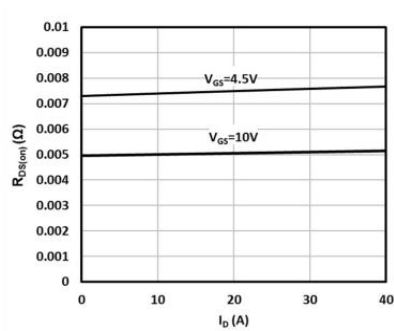


Fig.4 On-resistance vs. drain current

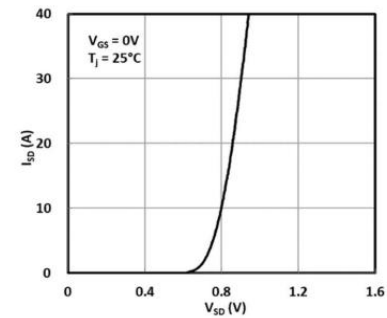


Fig.5 Source-to-drain diode forward characteristics

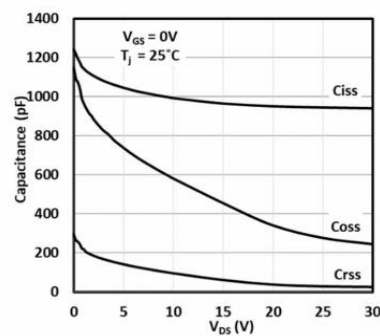


Fig.6 Capacitance vs. drain-to-source voltage

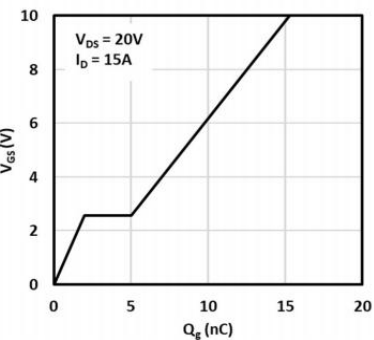


Fig.7 Gate-to-source voltage vs. gate charge

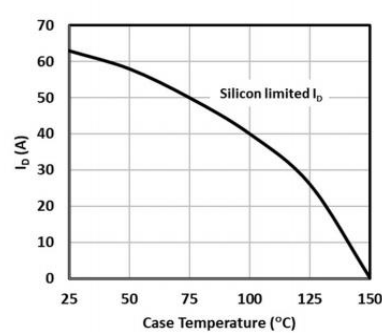


Fig.8 Maximum drain current vs. case temperature

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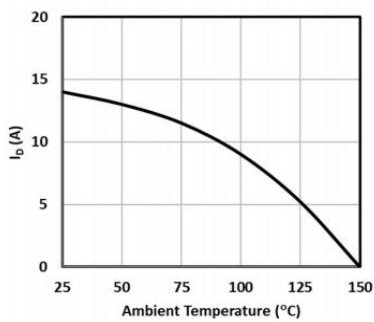
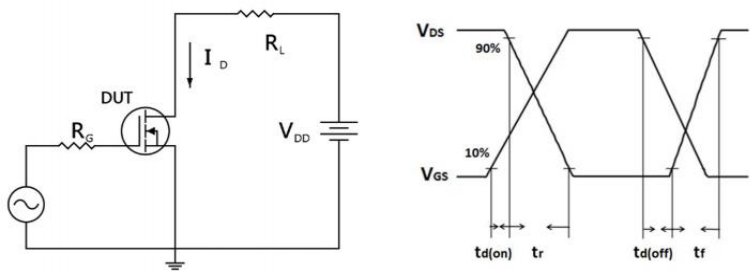
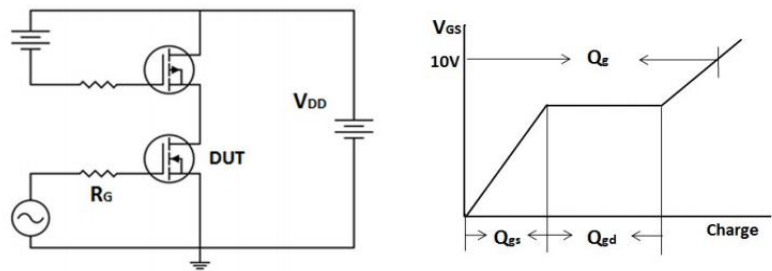


Fig. 9 Maximum drain current vs. ambient temperature

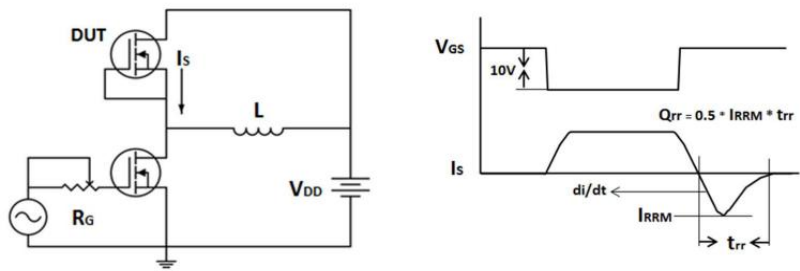
Test Circuits and Waveforms



Resistive switching time test circuit & waveforms

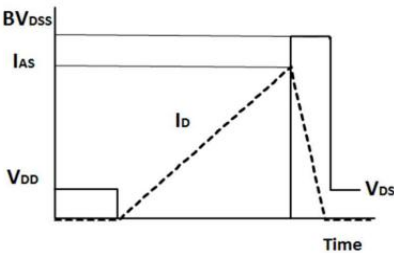
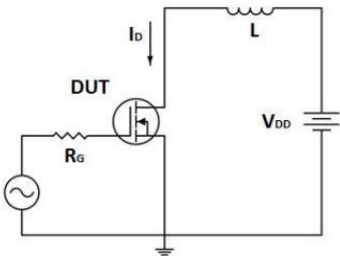


Gate charge test circuit & waveform



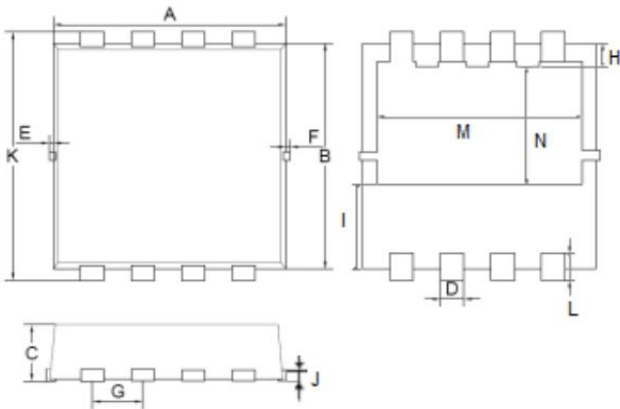
Peak diode recovery dv/dt test circuit & waveforms

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Unclamped inductive switching test circuit & waveforms

PDFN3*3-8L Package Information



PDFN3*3-8L		
Dimension	Min.	Max.
A	2.90	3.10
B	2.90	3.10
C	0.65	0.85
D	0.20	0.40
E	0.00	0.10
F	0.00	0.10
G	0.55	0.75
H	0.20	0.40
I	0.70	1.10
J	0.10	0.20
K	3.15	3.45
L	0.20	0.40
M	2.35	2.55
N	1.500	1.900

